MIL-PRF-38534 AND 38535 CERTIFIED FACILITY

600V/150A THREE PHASE BRIDGE 4853 Ny Sk WITH BRAKE

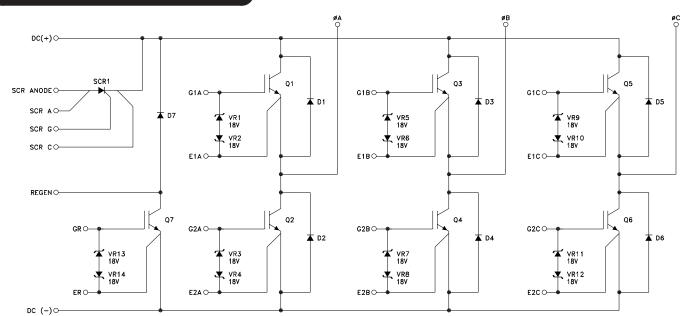
FEATURES:

- Replaces MSK4850
- Full Three Phase Bridge Configuration with SCR/IGBT Brake
- 600V Rated Voltage
- 150A Continuous Output Current
- Internal Zener Clamps on Gates
- Proprietary Encapsulation Provides Near Hermetic Performance
- HI-REL Screening Available (Modified 38534)
- Light Weight Domed ALSIC Baseplate
- · Robust Mechanical Design for Hi-Rel Applications
- Ultra-Low Inductance Internal Layout
- Withstands 96 Hours HAST and Thermal Cycling (-55°C to +125°C)

DESCRIPTION:

The MSK4853 is one of a family of plastic encapsulated modules (PEM) developed specifically for use in military, aerospace and other severe environment applications. The Three Phase Bridge configuration along with the SCR/IGBT brake circuit and 600 volt/150 Amp rating make it ideal for use in high current motor drive and inverter applications. The Aluminum Silicon Carbide (AISiC) baseplate offers superior flatness and light weight; far better than the copper or copper alloys found in most high power plastic modules. The high thermal conductivity materials used to construct the MSK4853 allow high power outputs at elevated baseplate temperatures. Our proprietary coating, SEES™ - Severe Environment Encapsulation System - protects the internal circuitry of MSK PEM's from moisture and contamination, allowing them to pass the rugged environmental screening requirements of military and aerospace applications. MSK PEM's are also available with industry standard silicone gel coatings for a lower cost option.

EQUIVALENT SCHEMATIC



TYPICAL APPLICATIONS

- Motor Drives
- Inverters

(8) ABSOLUTE MAXIMUM RATING

VCE	Collector to Emitter Voltage
Vge	Gate to Emitter Voltage±20V
IOUT	Current (Continuous)
IOUTP	Current Pulsed (1mS)
VCASE	Case Isolation Voltage

Storage Temperature Range ⁽⁹⁾ . -55°C to +125°C TST

- ΤJ
- Тс Case Operating Temperature Range

ELECTRICAL SPECIFICATIONS

Parameter (6)	Test Conditions	Giroup A		MSK4853H			MSK4853		
		Subgroup	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
		1	-	1.4	1.9	-	1.4	2.0	v
Collector-Emitter Saturation Volta	ge IC=150A, VGE=15V	2	-	1.5	2.1	-	-	-	V
	•	3	-	2.4	2.7	-	-	_	V
Collector Fritten Lonione Comment	+ VCE=600V VGE=0V	1	-	0.5	350	-	0.5	400	uA
Collector-Emitter Leakage Current		2	-	400	1700	-	-	-	uA
	IC=60mA, VCE=VGE	1	5.0	6.0	6.5	4.8	6.0	6.8	V
Gate Threshold Voltage		2	4.0	5.0	6.5	-	-	-	V
		3	5.0	6.5	7.5	-	-	-	V
		1	-	0.1	10	-	0.1	10	uA
Gate Leakage Current	$VCE=OV, VGE=\pm15V$	2	-	0.6	10	-	-	-	uA
		3	-	0.1	10	-	-	-	uA
		1	-	1.5	1.9	-	1.5	2.1	V
Diode Forward Voltage	IC=150A	2	-	1.2	1.9	-	-	-	V
		3	-	1.6	2.2	-	-	-	V
	VRRM=600V	1	-	0.01	15	-	0.01	18	mA
SCR Reverse Leakage		2	-	0.01	15	-	-	-	mA
		3	-	0.01	15	-	-	-	mA
	IF=100A	1	-	1.0	1.35	-	1.0	1.4	V
SCR On Voltage		2	-	1.0	1.35	-	-	-	V
		3	-	1.0	1.35	-	-	-	V
		1	-	100	300	-	100	325	mA
SCR Holding Current		2	-	90	300	-	-	-	mA
		3	-	110	300	-	-	-	mA
Regen Diode Forward Voltage	IF=50A	1	-	1.3	1.9	-	1.3	2.0	V
Total Gate Charge 🛈	V=300V, IC=150A	4	-	1.3	2.5	-	1.3	2.6	uC
E(on) ①	V=300V, Ic=150A, RG=5Ω, VGE=-7/+15V	4	-	2.5	-	-	2.5	-	mJ
	V=300V, Ic=75A, RG=5Ω, VGE=-7/+15V	4	-	1.2	3	-	1.2	4	mJ
E(off) ①	V=300V, IC=150A, RG=10Ω, VGE=-7/+15V	4	-	6.5	-	-	6.5	-	mJ
	V=300V, Ic=75A, RG=10Ω, VGE=-7/+15V	4	-	3.5	6	-	3.5	7	mJ
Diode Reverse Recovery Time (1)	lE=150, di/dt=2600A/uS	4	-	50	-	-	50	-	nS
	lE=75, di/dt=2600A/uS	4	-	45	-	-	45	-	nS
Diode Reverse Recovery Charge (1)	IE=150, di/dt=2600A/uS	4	-	2.0	_	-	2.0	-	uC
	IE=75, di/dt=2600A/uS	4	-	1.5	2.5	-	1.5	-	uC
Thermal Resistance (1)	IGBT @ TJ=125℃	-	-	0.22	0.26	-	0.22	0.26	°C/W
	DIODE @ TJ=125°C	-	-	0.35	0.41	-	0.35	0.41	°C/W

NOTES:

- Guaranteed by design but not tested. Typical parameters are representative of actual device performance but are for reference only.
- Industrial grade devices shall be tested to subgroup 1 unless otherwise specified.
- 10346 HI-REL grade devices ("H" suffix) shall be 100% tested to subgroups 1, 2 and sample tested to subgroup 3.
- Subgroup 4 testing available upon request.

Subgroup 1, 4 $T_A = +25^{\circ}C$

2, 5 TA = $+125^{\circ}C$ 3 $TA = -55^{\circ}C$

- All specifications apply to both the upper and lower sections of the half bridge.
- VGE=15V unless otherwise specified.
- 6789 Continuous operation at or above absolute maximum ratings may adversly effect the device performance and/or life cycle.
- Internal solder reflow temperature is 180°C, do not exceed.

THERMAL CALCULATIONS

Power dissipation and maximum allowable temperature rise involve many variables working together. Collector current, PWM duty cycle and switching frequency all factor into power dissipation. DC losses or "ON-TIME" losses are simply VCE(SAT) x Collector Current x PWM duty cycle. For the MSK4853, VCE(SAT)=1.9V max., and at 150 amps and a PWM duty cycle of 30%, DC losses equal 86 watts. Switching losses, in milli-joules, vary proportionally with switching frequency. The MSK4853 typical switching losses at VCE=300V and ICE=150A are about 9mJ, which is simply the sum of the turn-on switching loss and the turn-off switching loss. Multiplying the switching frequency times the switching losses will result in a power dissipation number for switching. The MSK4853, at 15KHz, will exhibit switching power dissipation of 135 watts. The total losses are the sum of DC losses plus switching losses, or in this case, 221 watts total.

221 watts x 0.26°C/W thermal resistance equals 57.5 degrees of temperature rise between the case and the junction. Subtracting 57.5°C from the maximum junction temperature of 150°C equals 92.5°C maximum case temperature for this example.

VCE(SAT) x IC x PWM duty cycle = 1.9V x 150 amps x 30% = 86 watts DC losses

Turn-on switching loss + Turn-off switching loss = Total switching losses = 2.5mJ + 6.5mJ = 9mJ

Total switching loss x PWM frequency = Total switching power dissipation = 9mJ x 15KHz = 135 watts

Total power dissipation = DC losses + switching losses = 86 + 135 = 221 watts

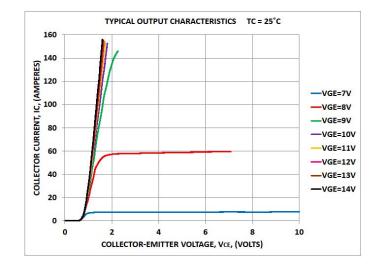
Junction temperature rise above case = Total power dissipation x thermal resistance

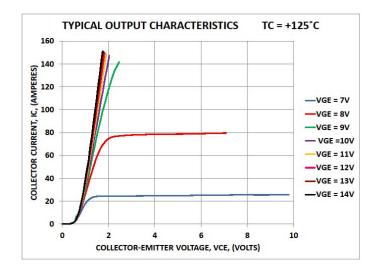
221 watts x 0.26°C/W = 57.5°C temperature rise above case

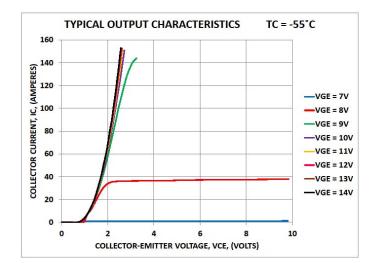
Maximum junction temperature - junction temperature rise = maximum baseplate temperature

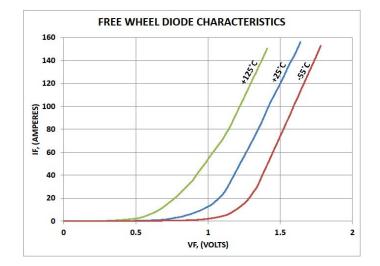
 $150^{\circ}\text{C} - 57.5^{\circ}\text{C} = 92.5^{\circ}\text{C}$

TYPICAL PERFORMANCE CURVES

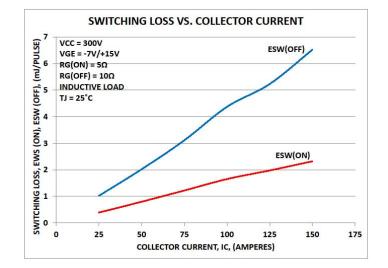


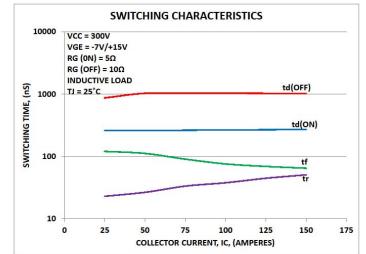


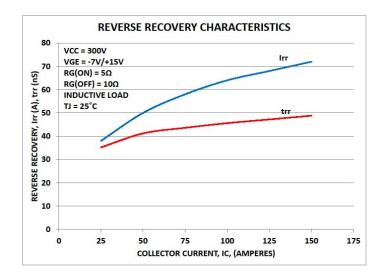




TYPICAL PERFORMANCE CURVES CONT'D



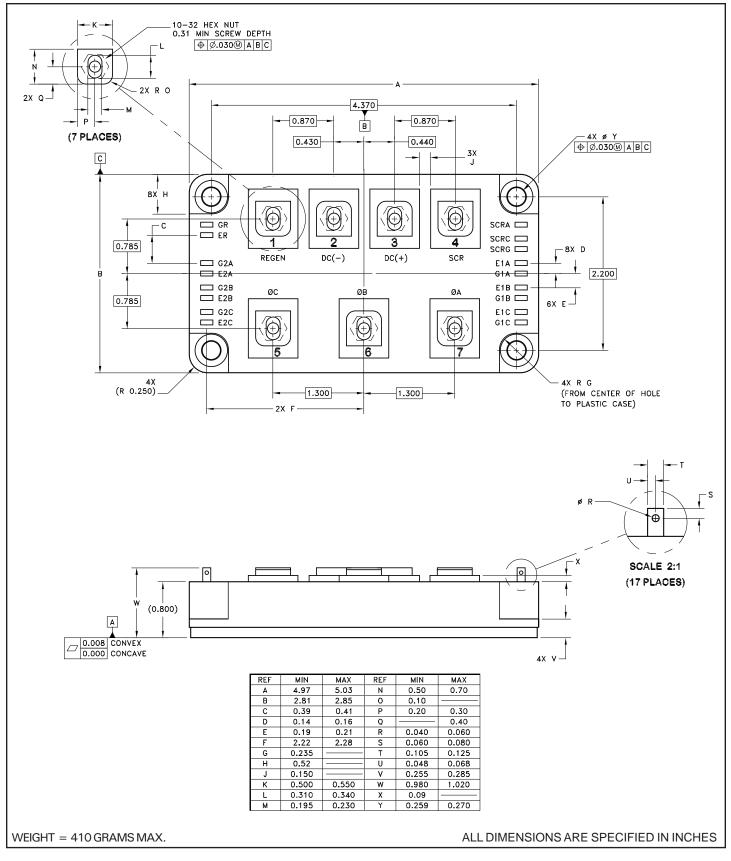




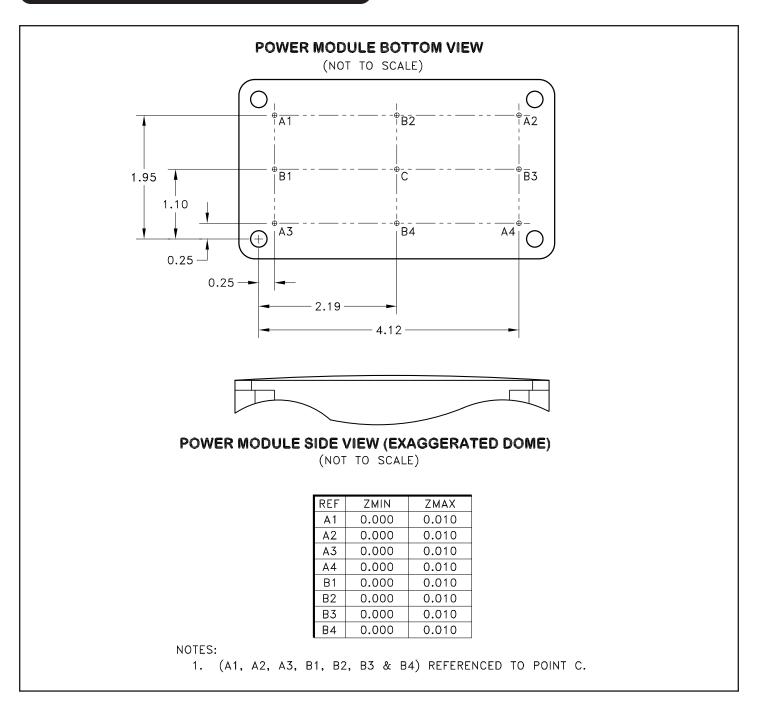
OPERATION	INDUSTRIAL	H SUFFIX			
QUALIFICATION (MODIFIED)	NO	YES			
ELEMENT EVALUATION	NO	YES			
CLEAN ROOM PROCESSING	YES	YES			
NON DESTRUCT BOND PULL SAMPLE	YES	YES			
CERTIFIED OPERATORS	NO	YES			
MIL LINE PROCESSING	YES	YES			
MAX REWORK SPECIFIED	NO	YES			
PRE-CAP VISUAL	YES – INDUSTRIAL	YES – CLASS H			
TEMP CYCLE (-55°C TO +125°C)	NO	YES			
BURN-IN	NO	YES – 160 HOURS			
ELECTRICAL TESTING	YES - 25°C	YES - FULL TEMP			
EXTERNAL VISUAL	YES – SAMPLE	YES			
PIN FINISH	NI	NI			

NOTE: ADDITIONAL SCREENING IS AVAILABLE SUCH AS XRAY, CSAM, MECHANICAL SHOCK, ETC. CONTACT FACTORY FOR QUAL STATUS.

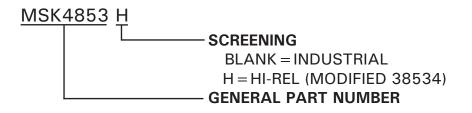
MECHANICAL SPECIFICATIONS



FOR CONVEX BASEPLATE PROFILE SEE SHEET 8



ORDERING INFORMATION



REVISION HISTORY

REV	STATUS	DATE	DESCRIPTION
F	Released	12/14	Add internal note and clarify mechanical specifications.

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